

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	13414	((438/96) or (438/97) or (438/149) or (438/150) or (438/151) or (438/166) or (438/299) or (438/308) or (438/364) or (438/378) or (438/479) or (438/482) or (438/486) or (438/487) or (438/488) or (438/491) or (438/585) or (438/694) or (438/710) or (438/795) or (438/913)).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/01/14 17:48
L2	103	1 and (anneal\$3 near4 (gate near2 insulat\$3))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/14 17:50
L3	44	2 and vacuum	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/14 17:50
S1	12368	((438/96) or (438/97) or (438/149) or (438/150) or (438/151) or (438/166) or (438/299) or (438/308) or (438/364) or (438/378) or (438/479) or (438/482) or (438/486) or (438/487) or (438/488) or (438/491) or (438/585) or (438/694) or (438/710) or (438/795) or (438/913)).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/01/14 17:48
S2	0	((gate near3 insulat\$4) same (anneal\$3 or heat\$3)) near5 vacuum	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/07/27 19:15
S3	0	((sio or (silicon near2 oxide)) same (anneal\$3 or heat\$3)) near5 vacuum	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/07/16 14:15
S4	0	((sio or (silicon near2 oxide)) and (anneal\$3 or heat\$3)) near5 vacuum	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/07/15 22:01

S5	12368	((438/96) or (438/97) or (438/149) or (438/150) or (438/151) or (438/166) or (438/299) or (438/308) or (438/364) or (438/378) or (438/479) or (438/482) or (438/486) or (438/487) or (438/488) or (438/491) or (438/585) or (438/694) or (438/710) or (438/795) or (438/913)).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/07/16 14:13
S6	112	((sio or (silicon near2 oxide)) same (anneal\$3 or heat\$3)) near5 vacuum	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/07/16 14:17
S7	6	((gate near3 insulat\$4) same (anneal\$3 or heat\$3)) near5 vacuum	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/07/16 14:15
S8	5	((((438/96) or (438/97) or (438/149) or (438/150) or (438/151) or (438/166) or (438/299) or (438/308) or (438/364) or (438/378) or (438/479) or (438/482) or (438/486) or (438/487) or (438/488) or (438/491) or (438/585) or (438/694) or (438/710) or (438/795) or (438/913)).CCLS.) and ((sio or (silicon near2 oxide)) same (anneal\$3 or heat\$3)) near5 vacuum)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/07/16 14:19
S9	1353	(poly near2 crystall\$8) same (poly near2 silicon)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/07/16 16:32
S10	455320	tft or (thin near2 film)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/07/16 14:21
S11	275	((poly near2 crystall\$8) same (poly near2 silicon)) same (tft or (thin near2 film))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/14 17:49

S12	291495	(anneal\$3 or heat\$3) same (vacuum or (low near2 pressure))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/07/16 14:29
S13	275	((poly near2 crystall\$8) same (poly near2 silicon)) same (tft or (thin near2 film))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/07/16 14:38
S14	54	((poly near2 crystall\$8) same (poly near2 silicon)) same (tft or (thin near2 film))) and ((anneal\$3 or heat\$3) same (vacuum or (low near2 pressure)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/07/16 14:24
S15	249811	(anneal\$3 or heat\$3) same (vacuum)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/07/16 14:36
S16	27	((poly near2 crystall\$8) same (poly near2 silicon)) same (tft or (thin near2 film))) and ((anneal\$3 or heat\$3) same (vacuum))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/07/16 14:30
S17	58093	(anneal\$3 or heat\$3) near3 (vacuum)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/07/16 14:39
S18	10	((poly near2 crystall\$8) same (poly near2 silicon)) same (tft or (thin near2 film))) and ((anneal\$3 or heat\$3) near3 (vacuum))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/07/16 14:37
S19	605	((poly near2 crystall\$8) same (poly near2 silicon)) and (tft or (thin near2 film))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/07/16 14:38
S20	5134	((anneal\$3 or heat\$3) near3 (vacuum)) same insulat\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/07/16 14:50
S21	2991	((anneal\$3 or heat\$3) near3 (vacuum)) near5 insulat\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/07/16 14:51

S22	1	((anneal\$3 or heat\$3) near3 (vacuum)) near5 insulat\$3) and (((poly near2 crystall\$8) same (poly near2 silicon)) and (tft or (thin near2 film)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/07/16 14:50
S23	9	((anneal\$3 or heat\$3) near3 (vacuum)) near5 (gate near3 insulat\$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/07/16 14:51
S24	3613	(anneal\$3 or heat\$3) near4 (insulat\$3 or (gate near2 insulat\$3)) near4 vacuum	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/07/16 16:32
S25	1353	(poly near2 crystall\$8) same (poly near2 silicon)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/07/16 16:32
S26	2	((anneal\$3 or heat\$3) near4 (insulat\$3 or (gate near2 insulat\$3)) near4 vacuum) and ((poly near2 crystall\$8) same (poly near2 silicon))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/07/16 16:33
S27	12423	((438/96) or (438/97) or (438/149) or (438/150) or (438/151) or (438/166) or (438/299) or (438/308) or (438/364) or (438/378) or (438/479) or (438/482) or (438/486) or (438/487) or (438/488) or (438/491) or (438/585) or (438/694) or (438/710) or (438/795) or (438/913)).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/07/27 19:15
S28	2538	((gate near5 (dielectric or insulat\$3 or oxide)) near10 anneal\$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/07/28 23:20

S29	412	(((438/96) or (438/97) or (438/149) or (438/150) or (438/151) or (438/166) or (438/299) or (438/308) or (438/364) or (438/378) or (438/479) or (438/482) or (438/486) or (438/487) or (438/488) or (438/491) or (438/585) or (438/694) or (438/710) or (438/795) or (438/913)).CCLS.) and (((gate near5 (dielectric or insulat\$3 or oxide)) near10 anneal\$3))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/07/27 19:17
S30	124905	vacuum near5 chamber	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/07/27 19:18
S31	12653	fns or ((fowler adj Nordheim) near2 stress)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/07/28 23:17
S32	69	(((438/96) or (438/97) or (438/149) or (438/150) or (438/151) or (438/166) or (438/299) or (438/308) or (438/364) or (438/378) or (438/479) or (438/482) or (438/486) or (438/487) or (438/488) or (438/491) or (438/585) or (438/694) or (438/710) or (438/795) or (438/913)).CCLS.) and (((gate near5 (dielectric or insulat\$3 or oxide)) near10 anneal\$3))) and (vacuum near5 chamber)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/07/27 19:19
S33	1	((((438/96) or (438/97) or (438/149) or (438/150) or (438/151) or (438/166) or (438/299) or (438/308) or (438/364) or (438/378) or (438/479) or (438/482) or (438/486) or (438/487) or (438/488) or (438/491) or (438/585) or (438/694) or (438/710) or (438/795) or (438/913)).CCLS.) and (((gate near5 (dielectric or insulat\$3 or oxide)) near10 anneal\$3))) and (vacuum near5 chamber)) and (fns or ((fowler adj Nordheim) near2 stress))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/07/27 19:19

S34	3	(((((438/96) or (438/97) or (438/149) or (438/150) or (438/151) or (438/166) or (438/299) or (438/308) or (438/364) or (438/378) or (438/479) or (438/482) or (438/486) or (438/487) or (438/488) or (438/491) or (438/585) or (438/694) or (438/710) or (438/795) or (438/913)).CCLS.) and (((gate near5 (dielectric or insulat\$3 or oxide)) near10 anneal\$3))) and (fns or ((fowler adj Nordheim) near2 stress)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/07/27 19:20
S35	212	((((gate near5 (dielectric or insulat\$3 or oxide)) near10 anneal\$3)) and (vacuum near5 chamber))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/07/27 19:21
S36	3	(((((gate near5 (dielectric or insulat\$3 or oxide)) near10 anneal\$3)) and (vacuum near5 chamber)) and (fns or ((fowler adj Nordheim) near2 stress)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/07/27 19:21
S37	0	"6638876".URPN.	USPAT	OR	OFF	2004/07/27 19:23
S38	24	("4585492" "5210056" "5578848" "5880040" "6020024" "6121130" "6136725" "6165834" "6168980" "6177363" "6191011" "6258690" "6274454" "6287897" "6291867" "6300203" "6306742" "6326231" "6326258" "6333557" "6335049" "6337289" "6338996" "6451713").PN.	USPAT	OR	OFF	2004/07/27 19:23
S39	3	(((((gate near5 (dielectric or insulat\$3 or oxide)) near10 anneal\$3)) and (fns or ((fowler adj Nordheim) near2 stress)))) and (((438/96) or (438/97) or (438/149) or (438/150) or (438/151) or (438/166) or (438/299) or (438/308) or (438/364) or (438/378) or (438/479) or (438/482) or (438/486) or (438/487) or (438/488) or (438/491) or (438/585) or (438/694) or (438/710) or (438/795) or (438/913)).CCLS.)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/07/27 19:25

S40	4	(((((gate near5 (dielectric or insulat\$3 or oxide)) near10 anneal\$3)) and (fns or ((fowler adj Nordheim) near2 stress))) and vacuum	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/07/27 19:26
S41	39	(((((gate near5 (dielectric or insulat\$3 or oxide)) near10 anneal\$3)) and (fns or ((fowler adj Nordheim) near2 stress)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/07/27 20:08
S42	211701	sio or (silicon near2 oxide)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/07/27 20:08
S43	29	(((((gate near5 (dielectric or insulat\$3 or oxide)) near10 anneal\$3)) and (fns or ((fowler adj Nordheim) near2 stress))) and (sio or (silicon near2 oxide))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/07/27 20:08
S44	529	((gate near5 (dielectric or insulat\$3 or oxide)) same (sio or (silicon near2 oxide)) near10 anneal\$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/07/27 20:24
S45	50	(fns or (fowler adj Nordheim)) near2 stress	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/07/27 20:25
S46	1	(((((gate near5 (dielectric or insulat\$3 or oxide)) same (sio or (silicon near2 oxide)) near10 anneal\$3)) and vacuum) and (fns or ((fowler adj Nordheim) near2 stress)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/07/27 20:26
S47	13	(((((gate near5 (dielectric or insulat\$3 or oxide)) same (sio or (silicon near2 oxide)) near10 anneal\$3)) and (fns or ((fowler adj Nordheim) near2 stress)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/07/27 20:30
S48	132	(((((gate near5 (dielectric or insulat\$3 or oxide)) same (sio or (silicon near2 oxide)) near10 anneal\$3)) and vacuum	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/07/27 20:40
S49	12653	fns or ((fowler adj Nordheim) near2 stress)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/07/28 23:17

S50	2538	((gate near5 (dielectric or insulat\$3 or oxide)) near10 anneal\$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/07/28 23:20
S51	4	(fns or ((fowler adj Nordheim) near2 stress)) same (((gate near5 (dielectric or insulat\$3 or oxide)) near10 anneal\$3))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/07/28 23:21
S52	0	(fns or ((fowler adj Nordheim) near2 stress)) near5 (((gate near5 (dielectric or insulat\$3 or oxide)) near10 anneal\$3))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/07/28 23:21
S53	2	(fns or ((fowler adj Nordheim) near2 stress)) near10 (((gate near5 (dielectric or insulat\$3 or oxide)) near10 anneal\$3))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/07/28 23:21